

# Mark Hopkinson

## List of Publications by Citations

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512  
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50  
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g-index

623  
ext. papers

10,877  
ext. citations

3  
avg, IF

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L-index

#	Paper	IF	Citations
512	Inverted electron-hole alignment in InAs-GaAs self-assembled quantum dots. <i>Physical Review Letters</i> , <b>2000</b> , 84, 733-6	7.4	433
511	Improved performance of 1.3 $\mu$ m multilayer InAs quantum-dot lasers using a high-growth-temperature GaAs spacer layer. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 704-706	3.4	221
510	Nature of the Stranski-Krastanow transition during epitaxy of InGaAs on GaAs. <i>Physical Review Letters</i> , <b>2001</b> , 86, 2381-4	7.4	220
509	Determination of the shape and indium distribution of low-growth-rate InAs quantum dots by cross-sectional scanning tunneling microscopy. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 1708-1710	3.4	184
508	Experimental investigation of the effect of wetting-layer states on the gain current characteristic of quantum-dot lasers. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 4904-4906	3.4	162
507	Charged and neutral exciton complexes in individual self-assembled In(Ga)As quantum dots. <i>Physical Review B</i> , <b>2001</b> , 63,	3.3	158
506	Optimizing the growth of 1.3 $\mu$ m InAs/InGaAs dots-in-a-well structure. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 2931-2936	2.5	154
505	Electronic energy levels and energy relaxation mechanisms in self-organized InAs/GaAs quantum dots. <i>Physical Review B</i> , <b>1996</b> , 54, 17738-17744	3.3	152
504	Emission spectra and mode structure of InAs/GaAs self-organized quantum dot lasers. <i>Applied Physics Letters</i> , <b>1998</b> , 73, 969-971	3.4	134
503	Observation of multicharged excitons and biexcitons in a single InGaAs quantum dot. <i>Physical Review B</i> , <b>2001</b> , 63,	3.3	132
502	Fast optical preparation, control, and readout of a single quantum dot spin. <i>Physical Review Letters</i> , <b>2008</b> , 100, 197401	7.4	120
501	Nuclear spin switch in semiconductor quantum dots. <i>Physical Review Letters</i> , <b>2007</b> , 98, 026806	7.4	117
500	Long-wavelength light emission and lasing from InAs/GaAs quantum dots covered by a GaAsSb strain-reducing layer. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 143108	3.4	111
499	Stranski-Krastanow transition and epitaxial island growth. <i>Physical Review B</i> , <b>2002</b> , 66,	3.3	109
498	1.3 [ $\mu$ m] InAs/GaAs multilayer quantum-dot laser with extremely low room-temperature threshold current density. <i>Electronics Letters</i> , <b>2004</b> , 40, 1412	1.1	104
497	Fine structure of charged and neutral excitons in InAs-Al <sub>0.6</sub> Ga <sub>0.4</sub> As quantum dots. <i>Physical Review B</i> , <b>2002</b> , 66,	3.3	103
496	High-performance three-layer 1.3- $\mu$ m InAs-GaAs quantum-dot lasers with very low continuous-wave room-temperature threshold currents. <i>IEEE Photonics Technology Letters</i> , <b>2005</b> , 17, 1139-1141	2.2	101

495	Quantum-confined Stark shifts of charged exciton complexes in quantum dots. <i>Physical Review B</i> , <b>2004</b> , 70,	3-3	99
494	Intraband relaxation via polaron decay in InAs self-assembled quantum dots. <i>Physical Review B</i> , <b>2004</b> , 70,	3-3	94
493	Mode structure of the L3 photonic crystal cavity. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 241117	3-4	85
492	Enhanced phonon-assisted absorption in single InAs/GaAs quantum dots. <i>Physical Review B</i> , <b>2001</b> , 63,	3-3	84
491	Surface band-gap narrowing in quantized electron accumulation layers. <i>Physical Review Letters</i> , <b>2010</b> , 104, 256803	7-4	80
490	Electric-field-dependent carrier capture and escape in self-assembled InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 4344-4346	3-4	77
489	Population inversion in a single InGaAs quantum dot using the method of adiabatic rapid passage. <i>Physical Review Letters</i> , <b>2011</b> , 106, 067401	7-4	75
488	Suppression of InAs/GaAs quantum dot decomposition by the incorporation of a GaAsSb capping layer. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 213105	3-4	75
487	InGaAs/AlAsSb/InP quantum cascade lasers operating at wavelengths close to 3 $\mu$ m. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 021108	3-4	74
486	Influences of the spacer layer growth temperature on multilayer InAs/GaAs quantum dot structures. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 1988-1992	2-5	74
485	Effect of thermal annealing and strain engineering on the fine structure of quantum dot excitons. <i>Physical Review B</i> , <b>2004</b> , 70,	3-3	73
484	p-doped 1.3 $\mu$ m InAs/GaAs quantum-dot laser with a low threshold current density and high differential efficiency. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 073113	3-4	72
483	Photocurrent spectroscopy of InAs/GaAs self-assembled quantum dots. <i>Physical Review B</i> , <b>2000</b> , 62, 16784-16791	3-5	71
482	Photoluminescence decay time measurements from self-organized InAs/GaAs quantum dots. <i>Journal of Applied Physics</i> , <b>1999</b> , 86, 2555-2561	2-5	72
481	Photoluminescence, photoluminescence excitation, and resonant Raman spectroscopy of disordered and ordered Ga <sub>0.52</sub> In <sub>0.48</sub> P. <i>Journal of Applied Physics</i> , <b>1993</b> , 73, 5163-5172	2-5	69
480	Dynamics of coherent and incoherent spin polarizations in ensembles of quantum dots. <i>Physical Review Letters</i> , <b>2004</b> , 93, 057401	7-4	66
479	Comparative study of InGaAs quantum dot lasers with different degrees of dot layer confinement. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 1-3	3-4	64
478	Optical transitions in type-II InAs/GaAs quantum dots covered by a GaAsSb strain-reducing layer. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 021102	3-4	62

477	Element-sensitive measurement of the hole nuclear spin interaction in quantum dots. <i>Nature Physics</i> , <b>2013</b> , 9, 74-78	16.2	61
476	In situ monitoring of the surface reconstructions on InP(001) prepared by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>1997</b> , 82, 474-476	2.5	59
475	Voltage enhancement in quantum well solar cells. <i>Journal of Applied Physics</i> , <b>1996</b> , 80, 1201-1206	2.5	59
474	Avalanche Multiplication in InAlAs. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 11-16	2.9	57
473	Room-temperature broadband emission of an InGaAs/GaAs quantum dots laser. <i>Optics Letters</i> , <b>2007</b> , 32, 44-6	3	57
472	Continuum transitions and phonon coupling in single self-assembled Stranski-Krastanow quantum dots. <i>Physical Review B</i> , <b>2003</b> , 68,	3.3	57
471	Excited states and selection rules in self-assembled InAs/GaAs quantum dots. <i>Physical Review B</i> , <b>1999</b> , 60, R2185-R2188	3.3	57
470	. <i>IEEE Journal of Quantum Electronics</i> , <b>2007</b> , 43, 1129-1139	2	56
469	Filamentation and linewidth enhancement factor in InGaAs quantum dot lasers. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 3251-3253	3.4	56
468	Magnetotunneling spectroscopy of dilute Ga(AsN) quantum wells. <i>Physical Review Letters</i> , <b>2003</b> , 91, 126802	3.4	55
467	Stacked low-growth-rate InAs quantum dots studied at the atomic level by cross-sectional scanning tunneling microscopy. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3758-3760	3.4	53
466	Structural analysis of strained quantum dots using nuclear magnetic resonance. <i>Nature Nanotechnology</i> , <b>2012</b> , 7, 646-50	28.7	52
465	Individual neutral and charged In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs quantum dots with strong in-plane optical anisotropy. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	52
464	Electronic band structure of AlGaInP grown by solid-source molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>1994</b> , 65, 213-215	3.4	52
463	Excess Avalanche Noise in $\text{In}_{0.52}\text{Al}_{0.48}\text{As}$ . <i>IEEE Journal of Quantum Electronics</i> , <b>2007</b> , 43, 503-507	2	50
462	Two-qubit conditional quantum-logic operation in a single self-assembled quantum dot. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	49
461	Broad-band superluminescent light-emitting diodes incorporating quantum dots in compositionally modulated quantum wells. <i>IEEE Photonics Technology Letters</i> , <b>2006</b> , 18, 58-60	2.2	49
460	Conduction-band discontinuity in InGaP/GaAs measured using both current-voltage and photoemission methods. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 474-476	3.4	48

459	InGaAs/AlAsSb quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 3992-3994	3-4	47
458	Photoluminescence spectroscopy of bandgap reduction in dilute InNAs alloys. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 182114	3-4	47
457	3.1 $\mu$ m room temperature InGaAs/AlAsSb/InP quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 031106	3-4	45
456	Atomic scale study of the impact of the strain and composition of the capping layer on the formation of InAs quantum dots. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 081707	2-5	43
455	Optical orientation and control of spin memory in individual InGaAs quantum dots. <i>Physical Review B</i> , <b>2005</b> , 72,	3-3	42
454	Band gap of completely disordered Ga <sub>0.52</sub> In <sub>0.48</sub> P. <i>Applied Physics Letters</i> , <b>1995</b> , 66, 3185-3187	3-4	42
453	Magneto-optical studies of self-organized InAs/GaAs quantum dots. <i>Physical Review B</i> , <b>1998</b> , 57, R2073-R2076	3-3	41
452	Improving optical properties of 1.55 $\mu$ m GaInNAs/GaAs multiple quantum wells with Ga(In)NAs barrier and space layer. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 4951-4953	3-4	41
451	Thermodynamic balance in quantum dot lasers. <i>Semiconductor Science and Technology</i> , <b>2001</b> , 16, 140-143	3-8	41
450	Optical mode loss and gain of multiple-layer quantum-dot lasers. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 2629-2631	3-4	41
449	Structural analysis of life tested 1.3 $\mu$ m quantum dot lasers. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 014913	2-5	40
448	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2010</b> , 16, 1015-1022	3-8	39
447	Low threshold current density and negative characteristic temperature 1.3 $\mu$ m InAs self-assembled quantum dot lasers. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 111102	3-4	39
446	Breakup of the conduction band structure of dilute GaAs <sub>1-x</sub> Ny alloys. <i>Physical Review B</i> , <b>2005</b> , 71,	3-3	39
445	Beating of exciton-dressed states in a single semiconductor InGaAs/GaAs quantum dot. <i>Physical Review Letters</i> , <b>2009</b> , 102, 207401	7-4	38
444	Role of segregation in InAs/GaAs quantum dot structures capped with a GaAsSb strain-reduction layer. <i>Physical Review B</i> , <b>2009</b> , 80,	3-3	37
443	Carrier lifetimes in type-II InAs quantum dots capped with a GaAsSb strain reducing layer. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 251905	3-4	37
442	Engineering carrier confinement potentials in 1.3- $\mu$ m InAs/GaAs quantum dots with InAlAs layers: Enhancement of the high-temperature photoluminescence intensity. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 3716-3718	3-4	37

441	Suppression of nuclear spin bath fluctuations in self-assembled quantum dots induced by inhomogeneous strain. <i>Nature Communications</i> , <b>2015</b> , 6, 6348	17.4	36
440	Polarized quantum dot emission from photonic crystal nanocavities studied under moderate resonant enhanced excitation. <i>Optics Express</i> , <b>2007</b> , 15, 17221-30	3.3	36
439	Structural and optical studies of vertically aligned InAs/GaAs self-assembled quantum dots. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 6374-6378	2.5	36
438	Strongly coupled single quantum dot in a photonic crystal waveguide cavity. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 111101	3.4	35
437	Charge separation and temperature-induced carrier migration in Ga <sub>1-x</sub> In <sub>x</sub> NyAs <sub>1-y</sub> multiple quantum wells. <i>Physical Review B</i> , <b>2011</b> , 84,	3.3	35
436	The effect of p doping in InAs quantum dot lasers. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 111113	3.4	35
435	Control of polarized single quantum dot emission in high-quality-factor microcavity pillars. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 051113	3.4	33
434	Energy level structure and electron relaxation times in InAs <sub>1-x</sub> Ga <sub>x</sub> As quantum dot-in-a-well structures. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 253502	3.4	33
433	Observation and Modeling of a Room-Temperature Negative Characteristic Temperature 1.3- $\mu\text{m}$ p-Type Modulation-Doped Quantum-Dot Laser. <i>IEEE Journal of Quantum Electronics</i> , <b>2006</b> , 42, 1259-1265	2	33
432	Tuning the structural and optical properties of 1.3- $\mu\text{m}$ InAs/GaAs quantum dots by a combined InAlAs and GaAs strained buffer layer. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3644-3646	3.4	33
431	Vertical-geometry all-optical switches based on InAs/GaAs quantum dots in a cavity. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 021109	3.4	31
430	Temperature dependence of threshold current in p-doped quantum dot lasers. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 151118	3.4	31
429	Whispering gallery resonances in semiconductor micropillars. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 071115	3.4	31
428	Nitrogen incorporation into strained (In, Ga) (As, N) thin films grown on (100), (511), (411), (311), and (111) GaAs substrates studied by photoreflectance spectroscopy and high-resolution x-ray diffraction. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 093522	2.5	30
427	Avalanche multiplication characteristics of Al <sub>0.8</sub> Ga <sub>0.2</sub> As diodes. <i>IEEE Transactions on Electron Devices</i> , <b>2001</b> , 48, 2198-2204	2.9	30
426	Intervalley scattering in GaAs/AlAs quantum cascade lasers. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 1378-1380	3.4	30
425	Photoluminescence of InNAs alloys: S-shaped temperature dependence and conduction-band nonparabolicity. <i>Physical Review B</i> , <b>2007</b> , 76,	3.3	29
424	Raman scattering by LO phonon-plasmon coupled modes in n-type In <sub>0.53</sub> Ga <sub>0.47</sub> As. <i>Physical Review B</i> , <b>2001</b> , 65,	3.3	29

423	1.3 [micro sign]m InAs/GaAs quantum-dot laser with low-threshold current density and negative characteristic temperature above room temperature. <i>Electronics Letters</i> , <b>2006</b> , 42, 922	1.1	28
422	Comparison of intraband absorption and photocurrent in InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 602-604	3.4	28
421	P-type delta doping in silicon MBE. <i>Thin Solid Films</i> , <b>1990</b> , 184, 15-19	2.2	28
420	As/P exchange on InP(001) studied by reflectance anisotropy spectroscopy. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 1423-1425	3.4	27
419	Observation of ultrahigh quality factor in a semiconductor microcavity. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 191109	3.4	27
418	Core-level photoemission spectroscopy of nitrogen bonding in GaN <sub>x</sub> As <sub>1-x</sub> alloys. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 1550-1552	3.4	27
417	Dilute nitride based double-barrier quantum-well infrared photodetector operating in the near infrared. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 3111-3113	3.4	27
416	Phase-matched second harmonic generation in asymmetric double quantum wells. <i>Applied Physics Letters</i> , <b>1998</b> , 72, 2654-2656	3.4	27
415	All-solid-state subpicosecond passively mode locked erbium-doped fiber laser. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 4-6	3.4	27
414	Endochondral Growth Defect and Deployment of Transient Chondrocyte Behaviors Underlie Osteoarthritis Onset in a Natural Murine Model. <i>Arthritis and Rheumatology</i> , <b>2016</b> , 68, 880-91	9.5	27
413	Thermal quenching of single localized excitons in GaInNAs layers. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 131903	3.4	26
412	Temperature-Dependent Gain and Threshold in P-Doped Quantum Dot Lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2007</b> , 13, 1261-1266	3.8	26
411	Strong in-plane polarized intraband absorption in vertically aligned InGaAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3415-3417	3.4	26
410	Modal gain and internal optical mode loss of a quantum dot laser. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 163-165	3.4	26
409	Quantum Dot Superluminescent Diodes for Optical Coherence Tomography: Skin Imaging. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2010</b> , 16, 748-754	3.8	25
408	Intraband magnetospectroscopy of singly and doubly charged n-type self-assembled quantum dots. <i>Physical Review B</i> , <b>2006</b> , 74,	3.3	25
407	Many-body effects in carrier capture and energy relaxation in self-organized InAs/GaAs quantum dots. <i>Physica B: Condensed Matter</i> , <b>1999</b> , 272, 12-14	2.8	25
406	Crack formation in III-V epilayers grown under tensile strain on InP(001) substrates. <i>Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties</i> , <b>1996</b> , 74, 383-393		25



405	Investigation of carrier dynamics on InAs quantum dots embedded in InGaAs/GaAs quantum wells based on time-resolved pump and probe differential photoluminescence. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 181924	3.4	24
404	Gain in p-doped quantum dot lasers. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 013107	2.5	24
403	Defect states and commensurability in dual-period Al <sub>x</sub> Ga <sub>1-x</sub> As photonic crystal waveguides. <i>Physical Review B</i> , <b>2003</b> , 68,	3.3	24
402	Hypomorphic conditional deletion of E11/Podoplanin reveals a role in osteocyte dendrite elongation. <i>Journal of Cellular Physiology</i> , <b>2017</b> , 232, 3006-3019	7	23
401	Long nuclear spin polarization decay times controlled by optical pumping in individual quantum dots. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	23
400	The onset of plasticity in nanoscale contact loading. <i>Proceedings of the Royal Society A: Mathematical, Physical and Engineering Sciences</i> , <b>2003</b> , 459, 2049-2068	2.4	23
399	. <i>IEEE Photonics Technology Letters</i> , <b>1993</b> , 5, 35-37	2.2	23
398	Temperature-dependent carrier tunneling for self-assembled InAs/GaAs quantum dots with a GaAsN quantum well injector. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 151104	3.4	22
397	High Q modes in elliptical microcavity pillars. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 161105	3.4	22
396	Influence of composition on the piezoelectric effect and on the conduction band energy levels of In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs quantum dots. <i>Journal of Applied Physics</i> , <b>2004</b> , 96, 5169-5172	2.5	22
395	Growth of strained InAs/InP quantum wells by molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 841-843	3.4	22
394	Effects of intermixing on modulation p-doped quantum dot superluminescent light emitting diodes. <i>Optics Express</i> , <b>2010</b> , 18, 7055-63	3.3	21
393	The effect of dead space on gain and excess noise in In <sub>0.48</sub> Ga <sub>0.52</sub> P p-n diodes. <i>Semiconductor Science and Technology</i> , <b>2003</b> , 18, 803-806	1.8	21
392	Direct observation of LO phonon-plasmon coupled modes in the infrared transmission spectra of n-GaAs and n-In <sub>x</sub> Ga <sub>1-x</sub> As epilayers. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	21
391	Optical characteristics of 1.55- $\mu$ m GaInNAs multiple quantum wells. <i>Applied Physics Letters</i> , <b>2004</b> , 85, 4013-4015	3.4	21
390	Site-Controlled Single-Photon Emitters Fabricated by Near-Field Illumination. <i>Advanced Materials</i> , <b>2018</b> , 30, e1705450	24	20
389	Atomic scale high-angle annular dark field STEM analysis of the N configuration in dilute nitrides of GaAs. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	20
388	Tuning Superluminescent Diode Characteristics for Optical Coherence Tomography Systems by Utilizing a Multicontact Device Incorporating Wavelength-Modulated Quantum Dots. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2009</b> , 15, 757-763	3.8	20



387	Stark shift of the spectral response in quantum dots-in-a-well infrared photodetectors. <i>Journal Physics D: Applied Physics</i> , <b>2007</b> , 40, 5537-5540	3	20
386	Mechanism for improvements of optical properties of 1.3- $\mu$ m InAs/GaAs quantum dots by a combined InAlAs/InGaAs cap layer. <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 083516	2.5	20
385	Influence of growth temperature on the structural and optical quality of GaInNAs/GaAs multi-quantum wells. <i>Semiconductor Science and Technology</i> , <b>2004</b> , 19, 813-818	1.8	20
384	Effect of hydrostatic pressure on the fragmented conduction band structure of dilute Ga(AsN) alloys. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	20
383	Mapping quantum dot-in-well structures on the nanoscale using the plasmon peak in electron energy loss spectra. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	20
382	Excess noise characteristics of Al/sub 0.8/Ga/sub 0.2/As avalanche photodiodes. <i>IEEE Photonics Technology Letters</i> , <b>2002</b> , 14, 522-524	2.2	20
381	Solid-source molecular beam epitaxy growth of GaInP and GaInP-containing quantum wells. <i>Journal of Applied Physics</i> , <b>1994</b> , 75, 2029-2034	2.5	20
380	Electrical control of fine-structure splitting in self-assembled quantum dots for entangled photon pair creation. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 221108	3.4	19
379	Coherency Strain as an Athermal Strengthening Mechanism. <i>Physical Review Letters</i> , <b>1997</b> , 78, 3912-3914	4.4	19
378	Intersublevel polaron dephasing in self-assembled quantum dots. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	19
377	Effect of facet angle on effective facet reflectivity and operating characteristics of quantum dot edge emitting lasers and superluminescent light-emitting diodes. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 081102	4.4	19
376	Determination of the outward relaxation of cleaved strained InAs structures by scanning tunneling microscopy. <i>Applied Surface Science</i> , <b>2002</b> , 190, 258-263	6.7	19
375	1.3 $\mu$ m lasers with AlInAs-capped self-assembled quantum dots. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 4710-4712	4.4	19
374	Room-temperature operation of an InAs/GaAs/AlAs quantum-cascade laser. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3409-3411	3.4	19
373	Temperature dependence of avalanche multiplication in submicron Al <sub>0.6</sub> Ga <sub>0.4</sub> As diodes. <i>Journal of Applied Physics</i> , <b>2002</b> , 92, 7684-7686	2.5	19
372	General characteristics of crack arrays in epilayers grown under tensile strain. <i>Semiconductor Science and Technology</i> , <b>2000</b> , 15, 325-330	1.8	19
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230	Coherence function control of Quantum Dot Superluminescent Light Emitting Diodes by frequency selective optical feedback. <i>Optics Express</i> , <b>2009</b> , 17, 13365-72	3.3	6
229	Effect of Dead Space on Low-Field Avalanche Multiplication in InP. <i>IEEE Transactions on Electron Devices</i> , <b>2007</b> , 54, 2051-2054	2.9	6
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225	Nonradiative Recombination in Multiple Layer In(Ga)As Quantum-Dot Lasers. <i>IEEE Journal of Quantum Electronics</i> , <b>2007</b> , 43, 698-703	2	6
224	Improved temperature performance of 1.31- $\mu\text{m}$ quantum dot lasers by optimized ridge waveguide design. <i>IEEE Photonics Technology Letters</i> , <b>2005</b> , 17, 1785-1787	2.2	6
223	RF-plasma source qualification and compositional characterisation of GaNAs superlattices using SIMS. <i>Applied Surface Science</i> , <b>2006</b> , 252, 7218-7220	6.7	6
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210	High reflectivity and low resistance 1.55- $\mu\text{m}$ Al <sub>0.65</sub> In <sub>0.35</sub> As/Ga <sub>0.63</sub> In <sub>0.37</sub> As strained quarter wave Bragg reflector stack. <i>Electronics Letters</i> , <b>1993</b> , 29, 1947	1.1	6
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205	Broadband, wide-angle antireflection in GaAs through surface nano-structuring for solar cell applications. <i>Scientific Reports</i> , <b>2020</b> , 10, 6269	4.9	5
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160	Intensity noise in quantum-dot laser diodes. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 3577-3579	3.4	4
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